

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	30	"0099533"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 10:43
L2	0	Transformer Coupled Plasma Source Technology	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 11:25
L3	77	Transformer Coupled Plasma Source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 11:26
L4	0	3 and (etch same metal same mask same silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 11:27
L5	0	3 and (etch same metal same silicon same chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 11:27
L6	1314	(etch same metal same silicon same chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 11:27
L7	307	(etch same metal same silicon same "same" same chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 11:27
L8	5	etch same (metal near silicon) same ("same" near chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:09
L9	569	(polyimide near resist) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:09

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L10	136	(polyimide near resist) same metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:12
L11	90	9 and 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:10
L12	2	11 and (metal near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:10
L13	41	polyimide same resist same (metal near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:10
L14	356	form near metal near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:17
L15	57	14 and polyimide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:58
L16	0	metal near mask near two near layers near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:59
L17	0	metal near mask near two near layers near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:59
L18	0	(metal near mask) same double near resist near layers	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 12:59
L19	0	(metal near mask) same (double near resist near layers)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:00

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L20	1	(metal near mask) same (two near resist near layers)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:00
L21	0	metal near bottom near resist near stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:01
L22	44	metal same (resist near stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:01
L23	0	(metal near mask) same (resist near stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:01
L24	12415	(metal near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:01
L25	265	(resist near stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:02
L26	0	24 sam 25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:02
L27	0	24 same 25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:02
L28	1	24 and 25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:02
L29	0	etching a resist stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:11

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L30	2	"5053318".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:14
L31	0	metal same mask same poltimide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:14
L32	0	(metal near mask) same poltimide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:14
L33	277	(metal near mask) same polyimide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:15
L34	41	(metal near mask) same polyimide same resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:15
L35	60	(metal near mask) same polyimide same photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:15
L36	84	34 or 35	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:30
L37	113	stacked near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:45
L38	29	"5891350"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:46
L39	2	"5891350".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:48

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L40	64721	metal same silicon same nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:49
L41	107	etch near "same" near chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 13:49
L42	35	40 and 41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 14:01
L43	2	"6143476".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 14:16
L44	0	42 and 43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 14:02
L45	480	decoupled plasma source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 14:19
L46	2728013	coupling or coupled	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 14:19
L47	414	45 and 46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 14:20
L48	186	polysilicon and 47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/07 14:33